

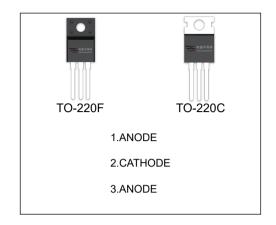
# MUR1640CT , MURF1640CT SUPER FAST

### MAIN CHARACTERISTICS

Io	16A
$V_{RRM}$	400 V
Tj	150 ℃
V <sub>F(typ)</sub>	1.1V (@Tj=125℃)

#### **FEATURES**

- Ultrafast 35ns Recovery Times
- High Voltage Capability to 400V
- Low Reverse Leakage Current



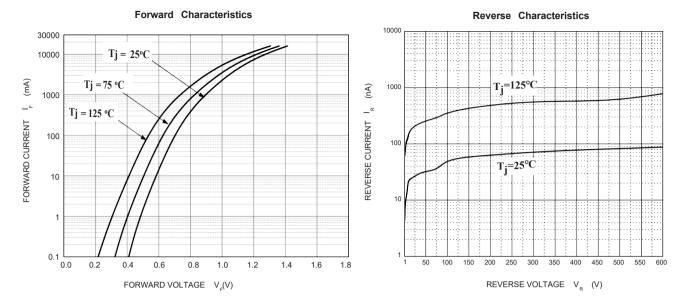
## MAXIMUM RATINGS ( $T_a$ =25°C unless otherwise noted )

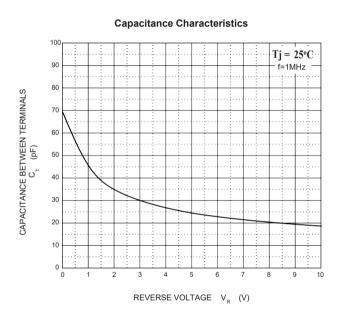
Symbol	Parameter	MU	MUR	
Symbol	Symbol Parameter		F1640CT	Unit
$V_{RRM}$	Peak repetitive reverse voltage			
V <sub>RWM</sub>	Working peak reverse voltage	4	400	
V <sub>R</sub>	DC blocking voltage			
V <sub>R(RMS)</sub>	RMS reverse voltage	2	280	
	Average rectified output current@ Per leg 8		8	А
Io	Average rectified output current@ Total device	1	16	
	Non-Repetitive peak forward surge current	120		Α
I <sub>FSM</sub>	8.3ms half sine wave	'	120	
P <sub>D</sub>	Power dissipation	2	2.0	
R <sub>OJA</sub>	Thermal resistance from junction to ambient	62	62.5	
T <sub>j</sub>	Operating Junction Temperature Range	-55 ~	-55 ~ +150	
T <sub>stg</sub>	Storage Temperature Range		-55 ~ +150	

#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit
Reverse voltage	V <sub>(BR)</sub>	I <sub>R</sub> =100uA		400			V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =400V	Tj =25℃		0.1	1	uA
			Tj =125℃		1.0		uA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =8.0A	Tj =25℃		1.22	1.4	V
			Tj =125℃		1.10		V
Typical total capacitance	C <sub>tot</sub>	V <sub>R</sub> =4.0V,f=1MHz			28		pF
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 0.5A, I <sub>R</sub> =1A,I <sub>rr</sub> =0.25A				35	ns







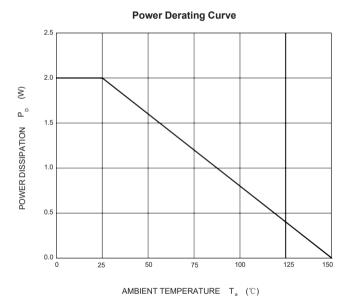


Diagram of circuit and Testing wave form of reverse recovery time

